

ZXTN04120HFF120V, SOT23F, NPN medium power Darlington transistor

Summary

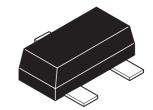
 $BV_{CEO} > 120V$

 $I_{C(cont)} = 1A$

 $V_{CE(sat)} < 1.5V @ 1A$

 $P_{D} = 1.5W$

Complementary part number ZXTP05120HFF

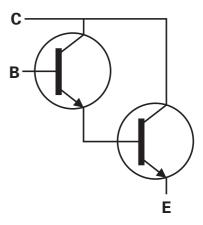


Description

This high performance NPN Darlington transistor is housed in the small outline SOT23 flat package for applications where space is at a premium.

Features

- · Darlington transistor
- 120 volt
- · 1 amp continuous rating
- · Small outline surface mount SOT23 flat package

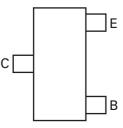


Applications

- · Lamp, relay and solenoid drive
- Lighting

Ordering information

| Device | Reel size | Tape width | Quantity |
|----------------|-----------|------------|----------|
| | (inches) | (mm) | per reel |
| ZXTN04120HFFTA | 7 | 8 | 3000 |



Pinout - top view

Device marking

1F6

Absolute maximum ratings

| Parameter | Symbol | Limit | Unit |
|---|-----------------------------------|-------------|-------|
| Collector-base voltage | V _{CBO} | 140 | V |
| Collector-emitter voltage | V _{CEO} | 120 | V |
| Emitter-base voltage | V _{EBO} | 10 | V |
| Continuous collector current (c) | I _C | 1 | Α |
| Peak pulse current | I _{CM} | 4 | Α |
| Base current | I _B | 0.5 | Α |
| Power dissipation @ T _{amb} =25°C ^(a) | P _D | 0.84 | W |
| Linear derating factor | | 6.72 | mW/°C |
| Power dissipation @ T _{amb} =25°C ^(b) | P _D | 1.34 | W |
| Linear derating factor | | 10.72 | mW/°C |
| Power dissipation @ T _{amb} =25°C ^(c) | P _D | 1.5 | W |
| Linear derating factor | | 12.0 | mW/°C |
| Power dissipation @ T _{amb} =25°C ^(d) | P _D | 2.0 | W |
| Linear derating factor | | 16.0 | mW/°C |
| Operating and storage temperature range | T _j , T _{stg} | - 55 to 150 | °C |

Thermal resistance

| Parameter | Symbol | Limit | Unit |
|------------------------------------|-----------------|-------|------|
| Junction to ambient ^(a) | $R_{\Theta JA}$ | 149 | °C/W |
| Junction to ambient ^(b) | $R_{\Theta JA}$ | 93 | °C/W |
| Junction to ambient ^(c) | $R_{\Theta JA}$ | 83 | °C/W |
| Junction to ambient ^(d) | $R_{\Theta JA}$ | 60 | °C/W |

NOTES:

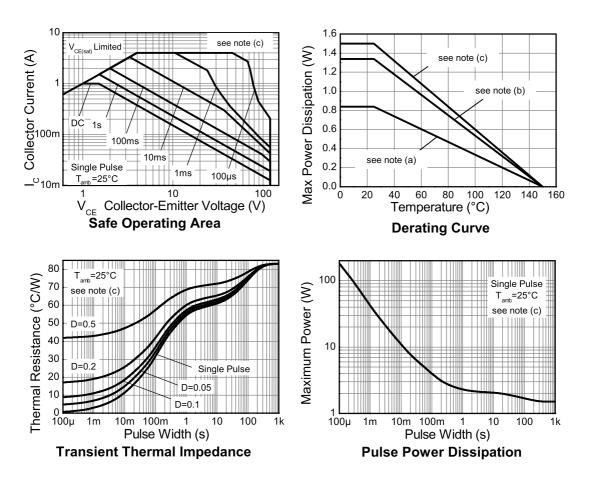
⁽a) For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions.

⁽b) Mounted on 25mm x 25mm x 1.6mm FR4 PCB with a high coverage of single sided 2oz copper in still air conditions.

⁽c) Mounted on 50mm x 50mm x 1.6mm FR4 PCB with a high coverage of single sided 2oz copper in still air conditions.

⁽d) As (c) above measured at t<5secs.

Characteristics



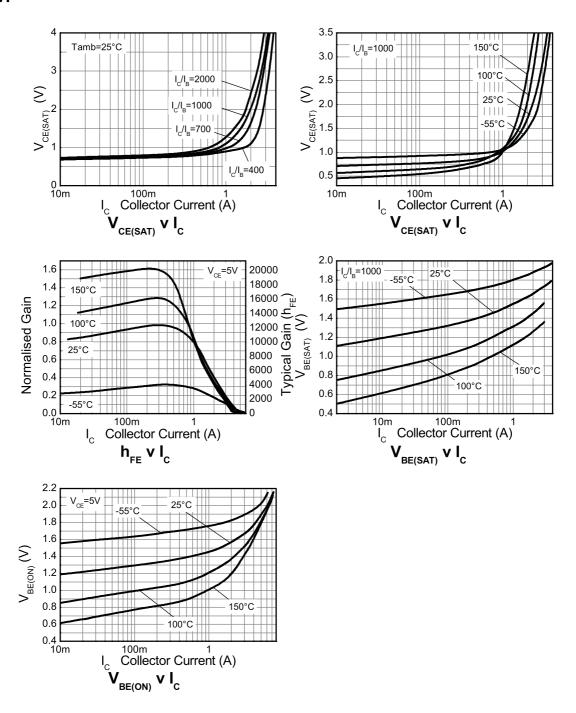
Electrical characteristics (at T_{amb} = 25°C unless otherwise stated)

| Parameter | Symbol | Min. | Тур. | Max. | Unit | Conditions |
|---|----------------------|------|------|------|------|---|
| Collector-base breakdown voltage | BV _{CBO} | 140 | 300 | | V | I _C = 100μA |
| Collector-emitter breakdown voltage (base open) | BV _{CEO} | 120 | 140 | | V | I _C = 10mA ^(*) |
| Emitter-base breakdown voltage | BV _{EBO} | 10 | 16 | | V | $I_E = 100 \mu A$ |
| Collector-base cut-off current | Ісво | | <1 | 100 | nA | V _{CB} = 120V |
| | | | | 10 | μΑ | $V_{CB} = 120V, T_{amb} = 100^{\circ}C$ |
| Collector-emitter cut-off current | I _{CES} | | <0.1 | 10 | μΑ | V _{CE} = 120V |
| Emitter-base cut-off current | I _{EBO} | | <1 | 100 | nA | V _{EB} = 8V |
| Collector-emitter saturation | V _{CE(sat)} | | 0.8 | 0.9 | V | $I_C = 250 \text{mA}, I_B = 0.25 \text{mA}^{(*)}$ |
| voltage | | | 1.1 | 1.5 | V | $I_C = 1A$, $I_B = 1mA^{(*)}$ |
| | | | 1.1 | 1.5 | V | $I_C = 2A$, $I_B = 5mA^{(*)}$ |
| Base-emitter saturation voltage | V _{BE(sat)} | | 1.55 | 1.70 | V | I _C = 1A, I _B = 1mA ^(*) |
| Base-emitter turn-on voltage | V _{BE(on)} | | 1.45 | 1.70 | V | $I_C = 1A$, $V_{CE} = 5V^{(*)}$ |
| Static forward current | h _{FE} | 3K | 11k | | | I _C = 50mA, V _{CE} = 5V ^(*) |
| transfer ratio | | 3K | 12k | | | $I_C = 500 \text{mA}, V_{CE} = 5V^{(*)}$ |
| | | 3K | 10k | 30K | | $I_C = 1A, V_{CE} = 5V^{(*)}$ |
| | | 1K | 5k | | | $I_C = 2A$, $V_{CE} = 5V^{(*)}$ |
| Transition frequency | f _T | | 120 | | MHz | I _C = 100mA, V _{CE} = 10V f = 20MHz |
| Input capacitance | C _{ibo} | | 68 | 90 | pF | V _{EB} = 500mV, f = 1MHz ^(*) |
| Output capacitance | C _{obo} | | 12.8 | 25 | pF | V _{CB} = 10V, f = 1MHz ^(*) |
| Delay time | t _d | | 507 | | ns | V _{CC} = 10V |
| Rise time | t _r | | 136 | | ns | $I_{C} = 500 \text{mA},$ $I_{B1} = I_{B2} = 0.5 \text{mA}$ |
| Storage time | t _s | | 910 | | ns | IB1 - IB2- 0.5IIIA |
| Fall time | t _f | | 369 | | ns | |

NOTES:

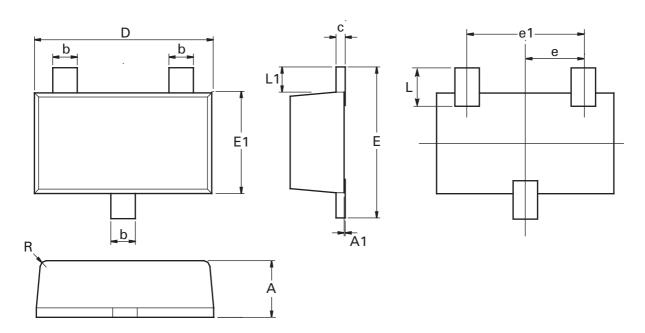
^(*) Measured under pulsed conditions. Pulse width ${\leq}300\mu s;$ duty cycle ${\leq}2\%.$

Typical characteristics



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Package outline - SOT23F



| Dim. | Millim | neters | Inc | hes | Dim. | Millimeters | | Inches | |
|------|--------|--------|--------|--------|------|-------------|------|--------|--------|
| | Min. | Max. | Min. | Max. | | Min. | Max. | Min. | Max. |
| Α | 0.80 | 1.00 | 0.0315 | 0.0394 | Е | 2.30 | 2.50 | 0.0906 | 0.0984 |
| A1 | 0.00 | 0.10 | 0.00 | 0.0043 | E1 | 1.50 | 1.70 | 0.0590 | 0.0669 |
| b | 0.35 | 0.45 | 0.0153 | 0.0161 | L | 0.48 | 0.68 | 0.0189 | 0.0268 |
| С | 0.10 | 0.20 | 0.0043 | 0.0079 | L1 | 0.30 | 0.50 | 0.0153 | 0.0161 |
| D | 2.80 | 3.00 | 0.1102 | 0.1181 | R | 0.05 | 0.15 | 0.0019 | 0.0059 |
| е | 0.95 | ref | 0.037 | 74 ref | 0 | 0° | 12° | 0° | 12° |
| e1 | 1.80 | 2.00 | 0.0709 | 0.0787 | - | - | - | - | - |

Note: Controlling dimensions are in millimeters. Approximate dimensions are provided in inches

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